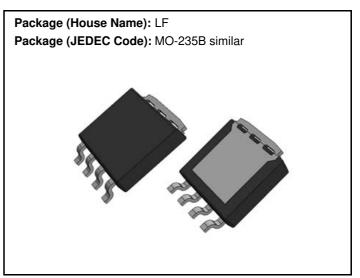
P50LF10SNK

Power MOSFETs 100V, 50A, N-channel

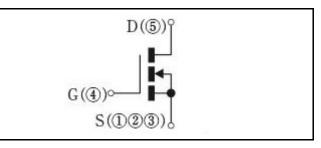
Feature

- N-channel
- Small SMD
- Large Current
- Low Ron
- 10V Gate Drive
- Low Capacitance
- · Based on AEC-Q101
- Halogen free
- Pb free terminal
- RoHS:Yes

OUTLINE



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 175	°C
Channel tempertature	Tch		-55 to 175	°C
Drain-source voltage	V _{DSS}		100	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	I _D		50	A
Continuous drain current(Peak)	I _{DP}	Pulse width 10µs, duty=1/100	200	Α
Total power dissipation	P _T		217	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	35	А
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≦150°C	140	mJ

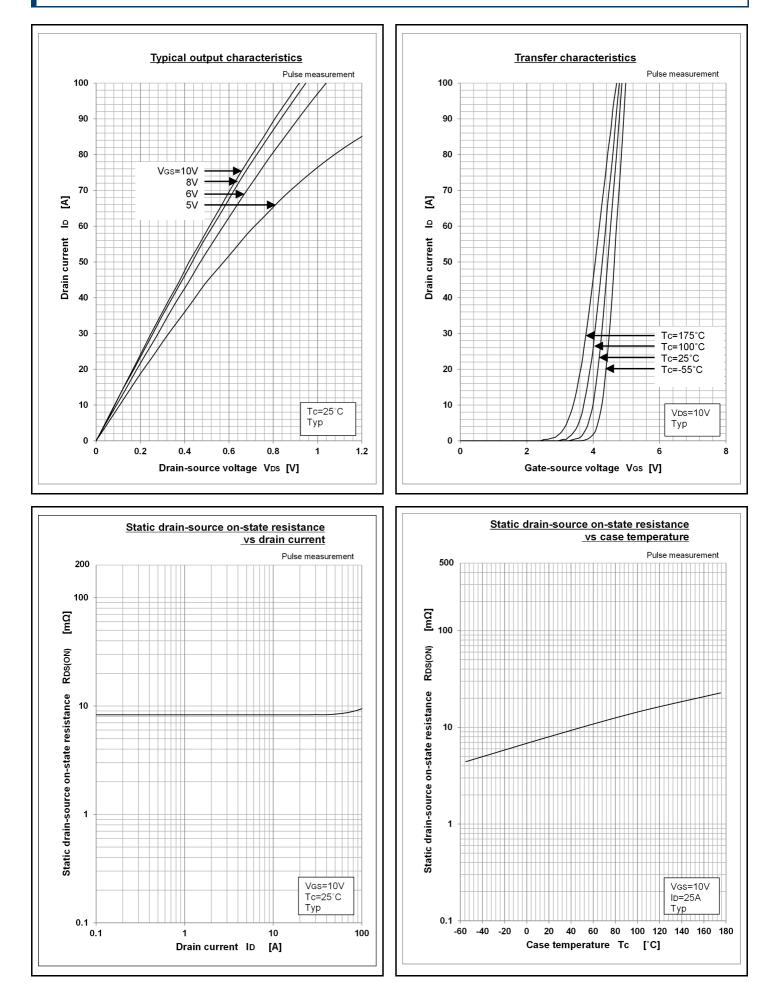
* : See the original Specifications

Electrical Characteristics	(unless otherwise specified : Tc=25°C)

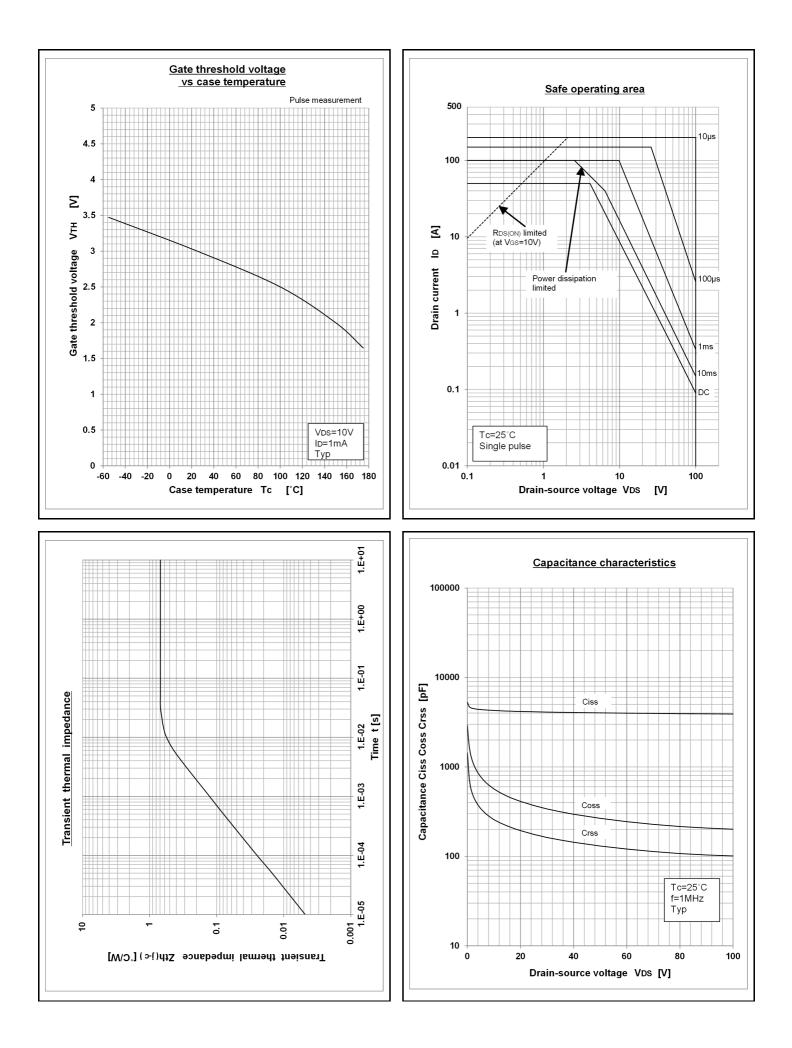
Item	Symbol	Conditions	Ratings			Unit
			MIN	ТҮР	MAX	Onit
Drain-Source breakdown voltage	V _{(BR)DSS}	ID=1mA, VGS=0V	100			V
Zero gate voltage drain current	I _{DSS}	VDS=100V, VGS=0V			1	μA
Gate-source leakage current	I _{GSS}	VGS=±20V, VDS=0V			±0.1	μA
Forward transconductance	g fs	ID=25A, VDS=10V	15			S
Static drain-source on-state resistance	R _{DS(ON)}	ID=25A, VGS=10V		0.0083	0.0104	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	2	3	4	V
Source-drain diode forward voltage	V_{SD}	IS=50A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case, with heatsink			0.69	°C/W
Total gate charge	Qg	VDD=80V, VGS=10V, ID=50A		80		nC
Gate to source charge	Qgs	VDD=80V, VGS=10V, ID=50A		21		nC
Gate to drain charge	Qgd	VDD=80V, VGS=10V, ID=50A		28		nC
Input capacitance	Ciss	VDS=25V, VGS=0V, f=1MHz		4130		pF
Reverce transfer capacitnce	Crss	VDS=25V, VGS=0V, f=1MHz		176		pF
Output capacitance	Coss	VDS=25V, VGS=0V, f=1MHz		370		pF
Turn-on delay time	td(on)	ID=25A, RL=2.00Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		7		ns
Rise time	tr	ID=25A, RL=2.00Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		11		ns
Turn-off delay time	td(off)	ID=25A, RL=2.00Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		57		ns
Fall time	tf	ID=25A, RL=2.00Ω, VDD=50V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		22		ns
Diode reverse recovery time	trr	IF=50A, VGS=0V, di/dt=100A/µs		58		ns
Diode reverse recovery charge	Qrr	IF=50A, VGS=0V, di/dt=100A/µs		123		nC

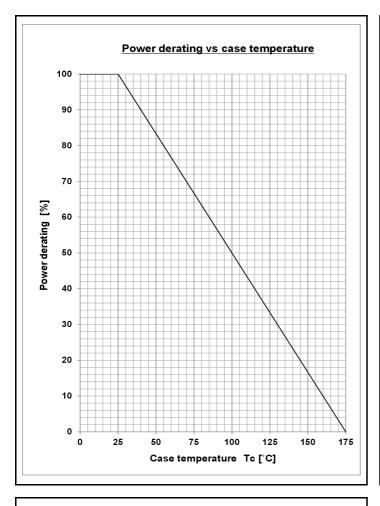
* : See the original Specifications

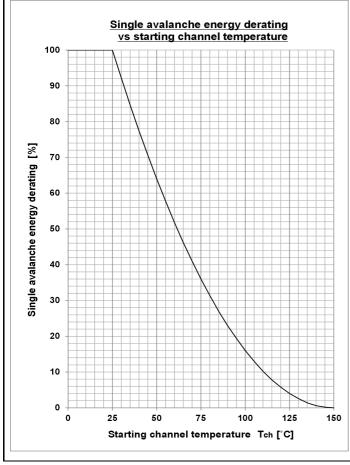
CHARACTERISTIC DIAGRAMS

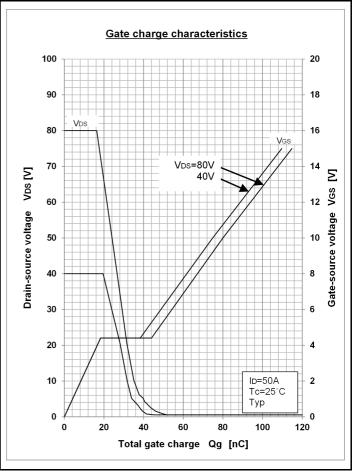


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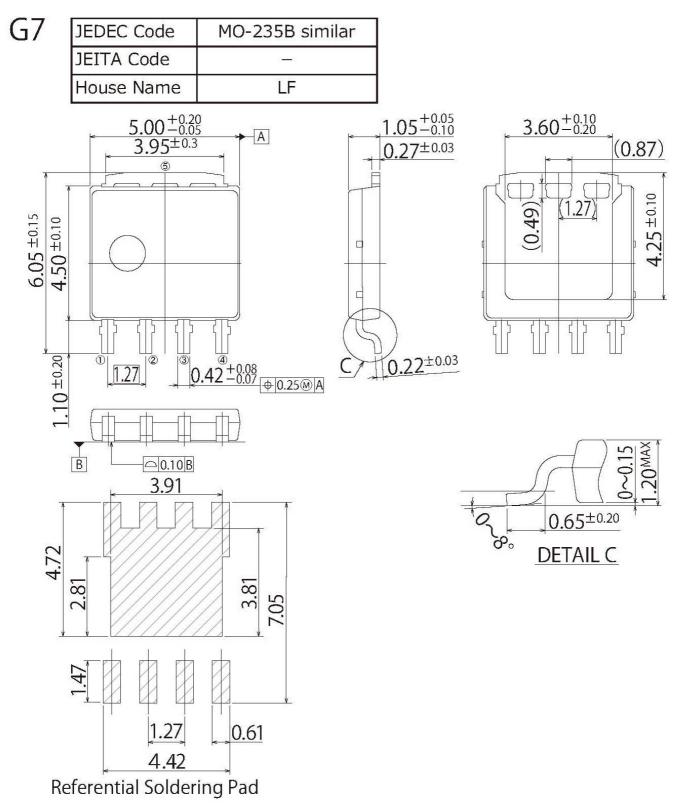








unit:mm



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[Specific applications]

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